

## NADAR SARSWATHI COLLEGE OF ENGINEERING AND TECHNOLOGY, THENI.

<b>Course/Branch :</b> B.E./CSE	<b>Year / Semester :</b> II/III	Format No.	NAC/TLP-07a.13
<b>Subject Code :</b> CS8351	<b>Subject Name :</b> Digital Principles and System Design	Rev. No.	02
<b>Unit No :</b> 5	<b>Unit Name :</b> Memory and Programmable Logic	Date	30.09.2020

### OBJECTIVE TYPE QUESTION BANK

S. No.	Objective Questions (MCQ /True or False / Fill up with Choices )	BTL
1	The instruction used in a program for executing them is stored in the _____ a) CPU b) Control Unit c) <b>Memory</b> d) Microprocessor	L2
2	A flip flop stores _____ a) 10 bit of information b) <b>1 bit of information</b> c) 2 bit of information d) 3-bit information	L2
3	The very first computer memory consisted of _____ a) A small display b) <b>A large memory storage equipment</b> c) An automatic keyboard input d) An automatic mouse input	L4
4	VLSI chip utilizes _____ a) NMOS b) CMOS c) BJT d) <b>All of the Mentioned</b>	L5
5	CD-ROM refers to _____ a) Floppy disk b) <b>Compact Disk-Read Only Memory</b> c) Compressed Disk-Read Only Memory d) Compressed Disk- Random Access Memory	L1
6	Which one of the following has capability to store data in extremely high densities? a) Register b) Capacitor c) <b>Semiconductor</b> d) Flip-Flop	L2
7	Data stored in an electronic memory cell can be accessed at random and on demand using a) Memory addressing b) <b>Direct addressing</b> c) Indirect addressing d) Control Unit	L2
8	The full form of PLD is _____ a) Programmable Large Device b) Programmable Long Device c) <b>Programmable Logic Device</b> d) Programmable Lengthy Device	L4
9	A ROM is defined as _____	L5

**NADAR SARSWATHI COLLEGE OF ENGINEERING AND TECHNOLOGY, THENI.**

<b>Course/Branch :</b> B.E./CSE	<b>Year / Semester :</b> II/III	<b>Format No.</b>	NAC/TLP-07a.13
<b>Subject Code :</b> CS8351	<b>Subject Name :</b> Digital Principles and System Design	<b>Rev. No.</b>	02
<b>Unit No :</b> 5	<b>Unit Name :</b> Memory and Programmable Logic	<b>Date</b>	30.09.2020

**OBJECTIVE TYPE QUESTION BANK**

	a) Read Out Memory b) Read Once Memory c) <b>Read Only Memory</b> d) Read One Memory	
10	ROM consist of _____ a) NOR and OR arrays b) NAND and NOR arrays c) <b>NAND and OR arrays</b> d) NOR and AND arrays	L1
11	For reprogrammability, PLDs use _____ a) PROM b) <b>EPROM</b> c) CDROM d) PLA	L2
12	The full form of PROM is _____ a) Previous Read Only Memory b) Programmable Read Out Memory c) <b>Programmable Read Only Memory</b> d) Previous Read Out Memory	L2
13	The full form of EPROM is _____ a) Easy Programmable Read Only Memory b) <b>Erasable Programmable Read Only Memory</b> c) Eradicate Programmable Read Only Memory d) Easy Programmable Read Out Memory	L4
14	PLDs with programmable AND and fixed OR arrays are called _____ a) <b>PAL</b> b) PLA c) APL d) PPL	L5
15	When both the AND and OR are programmable, such PLDs are known as _____ a) PAL b) PPL c) <b>PLA</b> d) APL	L1
16	ASIC stands for _____ a) Application Special Integrated Circuits b) Applied Special Integrated Circuits c) <b>Application Specific Integrated Circuits</b> d) Applied Specific Integrated Circuits	L2
17	The programmability and high density of PLDs make them useful in the design of _____ a) ISAC	L2

**NADAR SARSWATHI COLLEGE OF ENGINEERING AND TECHNOLOGY, THENI.**

<b>Course/Branch :</b> B.E./CSE	<b>Year / Semester :</b> II/III	Format No.	NAC/TLP-07a.13
<b>Subject Code :</b> CS8351	<b>Subject Name :</b> Digital Principles and System Design	Rev. No.	02
<b>Unit No :</b> 5	<b>Unit Name :</b> Memory and Programmable Logic	Date	30.09.2020

**OBJECTIVE TYPE QUESTION BANK**

	b) <b>ASIC</b> c) SACC d) CISF	
18	FPGA stands for _____ a) Full Programmable Gate Array b) Full Programmable Genuine Array c) First Programmable Gate Array d) <b>Field Programmable Gate Array</b>	L4
19	Which of the following is a reprogrammable gate array? a) EPROM b) FPGA c) <b>Both EPROM and FPGA</b> d) ROM	L5
20	The difference between FPGA and PLD is that _____ a) FPGA is slower than PLD b) FPGA has high power dissipation c) <b>FPGA incorporates logic blocks</b> d) All of the Mentioned	L1
21	Secondary memory is also known as _____ a) Registers b) Main Memory c) RAM d) <b>Both registers and main memory</b>	L2
22	In a computer, registers are present _____ a) Within control unit b) Within RAM c) Within ROM d) <b>Within CPU</b>	L2
23	Main memories of a computer, usually made up of _____ a) Registers b) <b>Semiconductors</b> c) Counters d) PLDs	L4
24	As the storage capacity of main memory is inadequate, which memory is used to enhance it? a) Secondary Memory b) Auxiliary Memory c) Static Memory d) <b>Both Secondary Memory and Auxiliary Memory</b>	L5
25	Which of the following comes under secondary memory/ies? a) Floppy disk b) Magnetic drum c) Hard disk d) <b>All of the Mentioned</b>	L1

**NADAR SARSWATHI COLLEGE OF ENGINEERING AND TECHNOLOGY, THENI.**

<b>Course/Branch :</b> B.E./CSE	<b>Year / Semester :</b> II/III	<b>Format No.</b>	NAC/TLP-07a.13
<b>Subject Code :</b> CS8351	<b>Subject Name :</b> Digital Principles and System Design	<b>Rev. No.</b>	02
<b>Unit No :</b> 5	<b>Unit Name :</b> Memory and Programmable Logic	<b>Date</b>	30.09.2020

**OBJECTIVE TYPE QUESTION BANK**

26	A sequential access memory is one in which _____ a) A particular memory location is accessed rapidly b) <b>A particular memory location is accessed sequentially</b> c) A particular memory location is accessed serially d) A particular memory location is accessed parallelly	L2
27	An example of sequential access memory is _____ a) Floppy disk b) Hard disk c) <b>Magnetic tape memory</b> d) RAM	L2
28	A Random Access Memory is one in which _____ a) Any location can be accessed sequentially b) <b>Any location can be accessed randomly</b> c) Any location can be accessed serially d) Any location can be accessed parallelly	L4
29	An example of RAM is _____ a) Floppy disk b) Hard disk c) Magnetic tape memory d) <b>Semiconductor RAM</b>	L5
30	Dynamic memory cells use _____ as the storage device. a) The reactance of a transistor b) The impedance of a transistor c) <b>The capacitance of a transistor</b> d) The inductance of a transistor	L1
31	To store 1-bit of information, how many transistor is/are used _____ a) <b>1</b> b) 2 c) 3 d) 4	L2
32	Static memory holds data as long as _____ a) AC power is applied b) <b>DC power is applied</b> c) Capacitor is fully charged d) High Conductivity	L2
33	In dynamic memory, CCD stands for _____ a) Charged Count Devices b) Change Coupled Devices c) <b>Charge Coupled Devices</b> d) Charged Compact Disk	L4
34	Volatile memory refers to _____ a) The memory whose loosed data is achieved again when power to the memory circuit is removed	L5

**NADAR SARSWATHI COLLEGE OF ENGINEERING AND TECHNOLOGY, THENI.**

<b>Course/Branch :</b> B.E./CSE	<b>Year / Semester :</b> II/III	<b>Format No.</b>	NAC/TLP-07a.13
<b>Subject Code :</b> CS8351	<b>Subject Name :</b> Digital Principles and System Design	<b>Rev. No.</b>	02
<b>Unit No :</b> 5	<b>Unit Name :</b> Memory and Programmable Logic	<b>Date</b>	30.09.2020

**OBJECTIVE TYPE QUESTION BANK**

	<p>b) <b>The memory which loses data when power to the memory circuit is removed</b></p> <p>c) The memory which loses data when power to the memory circuit is applied</p> <p>d) The memory whose loosed data is achieved again when power to the memory circuit is applied</p>	
35	<p>Non-volatile memory refers to _____</p> <p>a) <b>The memory whose loosed data is retained again when power to the memory circuit is removed/applied</b></p> <p>b) The memory which loses data when power to the memory circuit is removed</p> <p>c) The memory which loses data when power to the memory circuit is applied</p> <p>d) The memory whose loosed data is achieved again when power to the memory circuit is applied</p>	L1
36	<p>The example of non-volatile memory device is _____</p> <p>a) Magnetic Core Memory</p> <p>b) Read Only Memory</p> <p>c) Random Access Memory</p> <p>d) <b>Both Magnetic Core Memory and Read Only Memory</b></p>	L2
37	<p>Magnetic recording is the process of _____</p> <p>a) Storing data symmetrically</p> <p>b) Storing data sequentially</p> <p>c) <b>Storing data magnetically</b></p> <p>d) Both storing data symmetrically and</p>	L2
38	<p>Magnetic drum is a storage medium using _____</p> <p>a) The surface of a jumping magnetic drum</p> <p>b) <b>The surface of a rotating magnetic drum</b></p> <p>c) The surface of a stopped magnetic drum</p> <p>d) The surface of a moving magnetic drum</p>	L4
39	<p>By which technology, semiconductor memories are constructed?</p> <p>a) PLD</p> <p>b) LSI</p> <p>c) VLSI</p> <p>d) <b>Both LSI and VLSI</b></p>	L5
40	<p>Why did PROM introduced?</p> <p>a) To increase the storage capacity</p> <p>b) To increase the address locations</p> <p>c) <b>To provide flexibility</b></p> <p>d) To reduce the size</p>	L1